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Study of Irradiation Effect on Active Doping Profile in Silicon Detectors

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We used to measure total doping profile using Secondary Ion Mass Spectrometer (SIMS). But to study the effects of irradiation on the pixel silicon we need to know how is the doping profile is changing after the irradiation. This talk addresses the study of the irradiation effects on active doping profile by developing new promising method call Transfer Linear Method (TLM). The TLM method enables us to see the variation of electrically active dopant after the irradiation and to compare the active doping profiles before and after irradiation. For this test structures of four different wafers have been manufactured specially to characterize the active dopant concentration. In this talk I will show the first results of TLM method will be shown and discussed.

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